

12-36GHz Frequency Multiplier

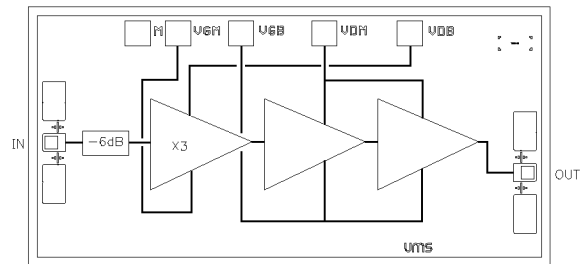
GaAs Monolithic Microwave IC

Preliminary

Description

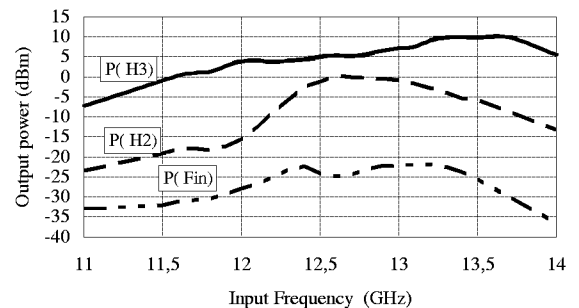
The CHX1094 is a cascaded by 3 frequency multiplier monolithic circuit. It is designed for a wide range of applications, from military to commercial communication systems. The backside of the chip is both RF and DC grounds. This helps simplify the assembly process.

The circuit is manufactured with a PM-HEMT process, 0.25µm gate length, via holes through the substrate, air bridges and electron beam gate lithography.



Main Features

- Broadband performances : 12-14GHz
- 5dBm output power for +14dBm input power
- DC bias : Vd=3.Volt @Id=40mA
- Chip size : 2.07 x 1.03 x 0.10 mm



typical measurement

Main Characteristics

Tamb. = 25°C

Symbol	Parameter	Min	Typ	Max	Unit
Fin	Input frequency range	12		14	GHz
Fout	Output frequency range	36		42	GHz
Pin	Input power		14		dBm
Pout	Output power @ Pin= 14dBm		5		dBm

ESD Protection : Electrostatic discharge sensitive device. Observe handling precautions !

Electrical Characteristics

$T_{amb} = +25^{\circ}\text{C}$, $V_d = 3\text{V}$, $V_{gm} = -1.6\text{V}$, $V_{gb} = -0.4\text{V}$.

Symbol	Parameter	Min	Typ	Max	Unit
F_{in}	Input frequency range	12		14	GHz
F_{out}	Output frequency range	36		42	GHz
P_{in}	Input power		14		dBm
P_{out}	Output power @ $P_{in}=14\text{dBm}$		5		dBm
$I_{s/2F_{in}}$	$2F_{in}$ level at the output ($P_{in} \leq 14\text{dBm}$)			0	dBm
$I_{s/F_{in}}$	F_{in} level at the output ($P_{in} \leq 14\text{dBm}$)			-20	dBm
VSWR _{in}	Input VSWR			2:1	
VSWR _{out}	Output VSWR			2.5:1	
I_d	Bias current		40		mA

Absolute Maximum Ratings

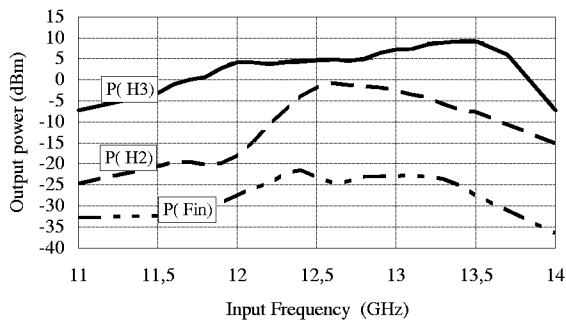
$T_{amb.} = 25^{\circ}\text{C}$ (1)

Symbol	Parameter	Values	Unit
V_d	Drain bias voltage	4	V
I_d	Drain bias current	120	mA
V_g	Gate bias voltage	-2 to +0.4	V
T_a	Operating temperature range	-40 to +85	$^{\circ}\text{C}$
T_{stg}	Storage temperature range	-55 to +155	$^{\circ}\text{C}$

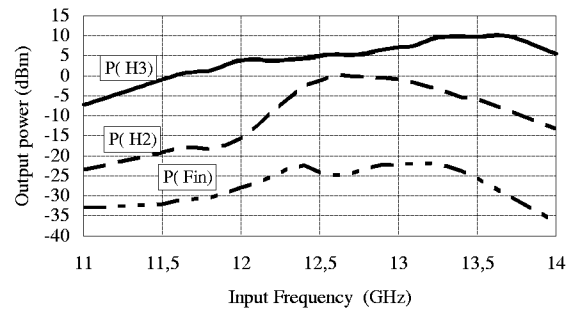
(1) Operation of this device above any of these parameters may cause permanent damage.

Typical on Jig Measurements.

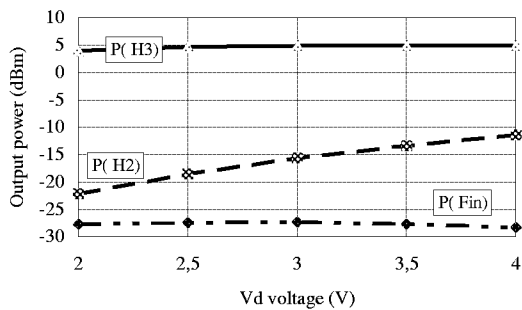
Bias conditions : $V_d = 2.5V$, $V_{gm} = -1.6V$, $V_{gb} = -0.4V$.



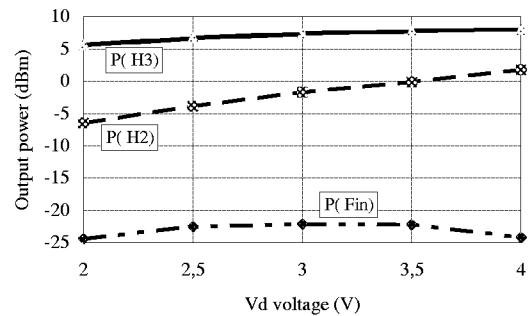
Pout versus Fin @ Pin=14 dBm & Vd=2.5V



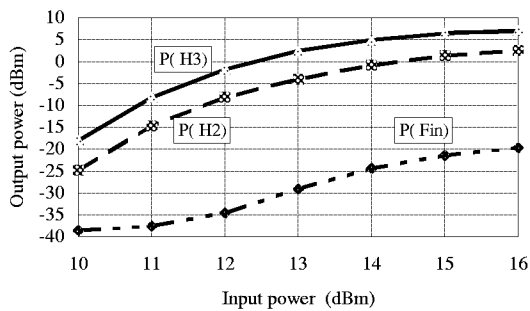
Pout versus Fin @ Pin=14 dBm & Vd=3V



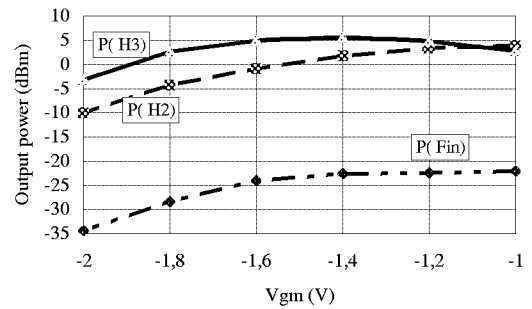
Pout versus Vd @ Pin=14dBm & Fin=13GHz



Pout versus Vd @ Pin=14dBm & Fin=12GHz

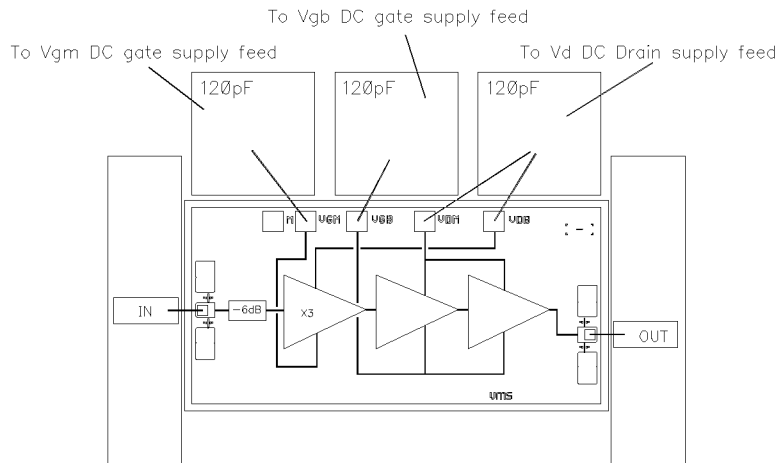


Pout versus Pin @ Fin=12.5GHz

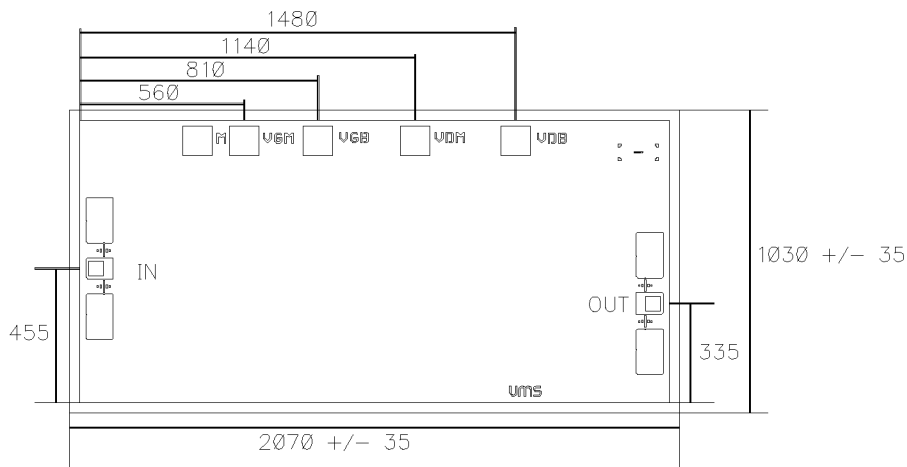


Pout versus Vgm @ Pin=14dBm & Fin=12.5GHz

Chip Assembly and Mechanical Data



Note : Supply feed should be capacitively bypassed. 25µm diameter gold wire is to be preferred
Bond Pad:100 x 100 µ²m.



Bonding pad positions.

(Chip thickness : 100µm. All dimensions are in micrometers)

Ordering Information

Chip form : CHX1094-99F/00

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